

Magneto-chiral vortex ratchet effect in two-dimensional arrays of φ_0 -Josephson junctions

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We demonstrate transport in 2D arrays of multiterminal φ_0 -junctions. When applying an in-plane magnetic field we observe nonreciprocal vortex depinning currents, induced by a ratchet-like pinning potential. The ratchet effect is explained as a consequence of spontaneous supercurrents that arise in the presence of next-nearest neighbor Josephson couplings. Tuning the density of vortices to commensurate values of the frustration parameter results in an enhancement of the ratchet effect. In addition, we find a surprising sign reversal of the ratchet effect near frustration $1/3$.

The equilibrium supercurrent in Josephson junctions is independent of the polarity of the phase bias when time-reversal or space-inversion symmetry are granted. If both symmetries are lifted, the current-phase-relation (CPR) is no longer odd under inversion of phase bias. The first experimental evidence for this asymmetry in an individual junction was the discovery of the anomalous Josephson effect, i.e., a finite shift φ_0 in phase of the CPR. Such φ_0 -junction behavior has been demonstrated in systems with large spin-orbit interaction (SOI) [1–5]. More recently, similar devices have also featured nonreciprocal critical currents, referred to as Josephson diode effect (JDE) [6–14]. As shown in Ref. [15], the anomalous φ_0 -shift and JDE can coexist in the same device.

What is the manifestation of the φ_0 -shift when φ_0 -junctions are integrated into 2D Josephson junction arrays (JJAs)? JJAs provide an important paradigm in condensed matter physics by enabling the study of fundamental properties of 2D superconductors in a highly controllable fashion [16]. They have been important as model systems for many-body phenomena such as the Berezinski-Kosterlitz-Thouless transition [17–21], quantum phase transitions [22–25], phase locking and synchronized emission [26, 27], and macroscopic quantum effects [28–30]. In perpendicular magnetic fields, the resistive state of the arrays is controlled by vortex dynamics. The vortex depinning current displays striking commensurability effects at fractional values of the frustration $f = \Phi/\Phi_0$ [31–34], where Φ is the magnetic flux threading a plaquette and Φ_0 is the superconducting flux quantum.

Tuning the φ_0 -shift by an in-plane magnetic field introduces a novel knob for controlling JJAs. For the simplest case of square arrays with nearest neighbor Josephson coupling only, a uniform φ_0 -shift in all junctions can be gauged out and has no experimentally observable consequences. It is an open question, under which conditions the φ_0 -shift has an observable impact on the transport characteristics of JJAs.

In this Letter, we report on two-dimensional square arrays made of φ_0 -junctions. Applying an in-plane magnetic

field with a component perpendicular to the current, we observe nonreciprocal vortex depinning currents. At frustrations $f \ll 1$, the nonreciprocity persists up to fairly large in-plane fields and temperatures. This effect is explained in terms of a field-tunable, ratchet-like shape of the vortex pinning potential, which we deduce from a minimal model of the JJA with both nearest and next-nearest neighbor Josephson couplings with anomalous φ_0 -shifts. Vortex nonreciprocity also occurs at fractional f , with inverted sign for $f \approx 1/3$.

In our devices, the 2DEG is located in a shallow InGaAs/InAs/InGaAs quantum well, whose characteristics are described in detail in the Supplementary Information. Superconductivity in the 2DEG is introduced by proximity to an epitaxially-grown Al film [35]. Using electron beam lithography followed by selective wet-etching of the Al film, we define a square array of 200×200 aluminum islands separated by 100 nm wide gaps where the aluminum is removed. The islands are 400×400 nm² in size. A global top-gate allows us to control the electron density in the weak links.

For $\Phi \ll \Phi_0$, the square JJAs (lattice constant a) feature an intrinsic vortex pinning potential $U(x, y) \approx E_B [\cos(2\pi x/a) + \cos(2\pi y/a)]$ with minima of the potential located near the corners of the superconducting islands, as illustrated in Fig. 1a. When applying a transport current with density \vec{j} , vortices experience a Lorentz force $\vec{F}_L = \Phi_0 \vec{j} \times \vec{z}$ perpendicular to the applied current. Depinning of vortices occurs when the Lorentz force exceeds the maximal gradient of the pinning potential. For a single vortex in a square array the depinning current density is $j_c = 2\pi E_B/a\Phi_0$, which is approximately 10% of the critical current density of the individual junctions [16, 23, 36].

To link the observed nonreciprocal vortex depinning current to the anomalous phase shifts, we transcend the XY model with only nearest neighbor couplings and take the multi-terminal character [37, 38] of the junctions into account. Microscopically, Andreev bound states (ABS) in the weak links connect not only nearest neighbor Al islands, but to a lesser extent also

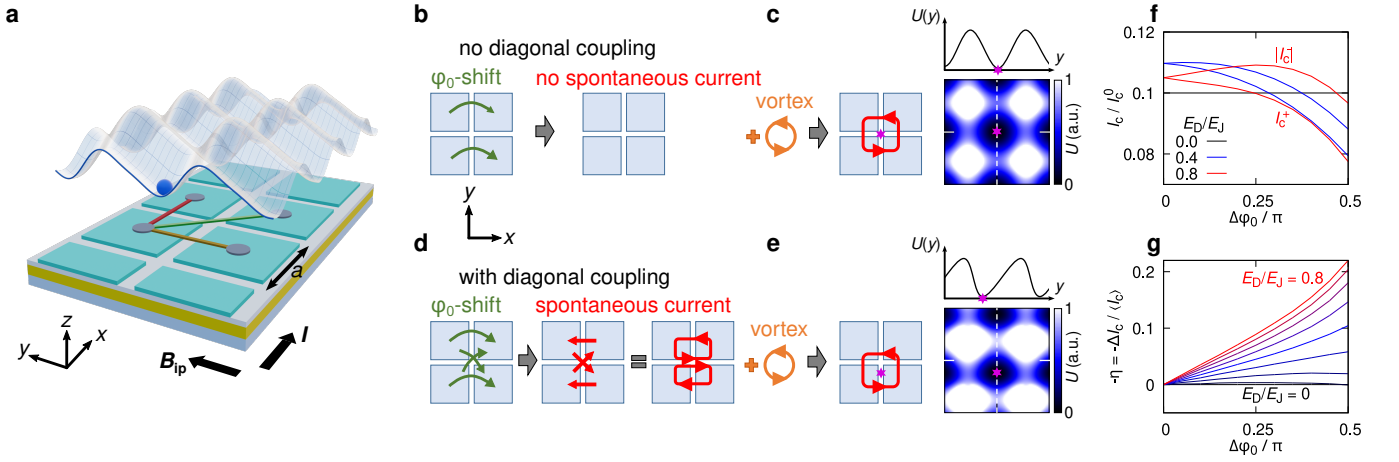


FIG. 1. **a**, Two-dimensional square Josephson junction array (JJA) with surface plot showing the vortex pinning potential $U(x, y)$, the bias current I , and the applied in-plane magnetic field B_{ip} . The JJA is modeled using both (red, orange) neighbor and next-nearest (green) neighbor Josephson couplings between superconducting islands. The lattice constant of the array is $a = 500$ nm. **b**, JJA with nearest neighbor coupling only, with no spontaneous supercurrent in the ground state. **c**, Sketch of the Josephson currents for a vortex in absence of diagonal coupling. The Josephson current distribution remains four-fold symmetric. A color plot of the vortex pinning potential is shown on the right. Vortices driven in the y -direction experience a sinusoidal pinning potential $U(y)$, as sketched above the color plot of $U(x, y)$. **d**, Anomalous phase shifts $\varphi_0^x > \varphi_0^{\text{diag}}$ and persistent currents for the case with diagonal coupling. **e**, Sketch of the Josephson currents for a vortex in the case with diagonal coupling. The corresponding vortex pinning potential $U(x, y)$ is skewed. Vortices driven in the y -direction experience a ratchet-like potential $U(y)$, as sketched above the color plot of $U(x, y)$ [$U(y)$ shown with exaggerated skewness for better visibility]. **f**, Numerical simulation of vortex depinning currents. The phase shift parameter $\Delta\varphi_0$ is the difference between horizontal and diagonal phase shifts: $\Delta\varphi_0 = \varphi_0^x - \varphi_0^{\text{diag}}$. E_D/E_J is the ratio between diagonal and non-diagonal Josephson couplings. **g**, Resulting rectification efficiency $\eta = \Delta I_c / \langle I_c \rangle$ extracted from the numerical simulation of positive and negative depinning currents. The diagonal coupling is changed in steps of 0.1 from 0 to 0.8.

next-nearest neighbors as indicated in Fig. 1a (green line). With in-plane magnetic fields along the \hat{y} direction, the diagonal junctions also exhibit a non-zero phase shift φ_0^{diag} , which in general differs from the phase shift φ_0^x of the junctions in the x -direction. The additional diagonal couplings render the ground state frustrated even without perpendicular magnetic field: The sums of φ_0 -shifts around closed loops no longer cancel. To maintain fluxoid quantization within the plaquettes, spontaneous supercurrents emerge in the ground state, see Fig. 1d. The current configuration in the ground state has an (up-down) reflection symmetry about the current axis. This symmetry is broken when a vortex is added to the array, as shown in Fig. 1e. The vortex pinning potential $U(x, y)$ shown on the right side of Fig. 1e no longer exhibits fourfold rotational symmetry and $U(x = 0, y)$ exhibits a ratchet-like dependence (see the Supplemental Information for calculational details).

We can compute the vortex depinning currents by minimizing the free energy of the JJA with a single vortex located within the array. The depinning current is obtained as the largest bias current, for which the vortex remains localized (for details, see the Supplemental Information). The results are plotted in Fig. 1f as a function of the difference $\Delta\varphi_0 = \varphi_0^x - \varphi_0^{\text{diag}}$ between horizontal and diagonal phase shifts. The phase shift affects the depinning currents only when the coupling E_D between next-nearest neighbors is turned on and results in a nonreciprocal depinning current. The corresponding diode efficiencies $\eta \equiv (I_c^+ - |I_c^-|) / \langle I_c \rangle$ (with

$\langle I_c \rangle \equiv (I_c^+ + |I_c^-|) / 2$) are shown in Fig. 1g and reach up to 20% for $\Delta\varphi_0 = \pi/2$ and $E_D = 0.8$.

Figure 2 shows dc transport data in the regime of very dilute vortices (frustration $f \ll 1$, where $f = B_z/B_0$ with $B_0 = \Phi_0/a^2 = 8.2$ mT). Panel a shows $V(I)$ -characteristics with an in-plane field $B_{ip} = 250$ mT applied perpendicular (purple) and parallel (green) to the direction of the transport current. A large rectification η is observed for $\vec{j} \perp \vec{B}_{ip}$, while η is negligible for the parallel configuration. This is a new type of *vortex-diode effect*, which is distinct from the JDE [7] that can occur at much higher current densities, close to the Josephson critical current density.

To quantify the degree of nonreciprocity, Figs. 2b-d show the rectification efficiency $\eta \equiv (I_c^+ - |I_c^-|) / \langle I_c \rangle$ (with $\langle I_c \rangle \equiv (I_c^+ + |I_c^-|) / 2$) as a function of out-of-plane field B_z and gate voltage for different orientations of \vec{B}_{ip} . We notice that (i) the rectification coefficient is large, reaching a maximum of 0.4; (ii) η is very sensitive to the out-of-plane field, showing a few- μ T-wide peak near $B_z = 0$; (iii) $\eta(B_y, B_z) \approx -\eta(-B_y, B_z)$ and $\eta(B_y, B_z) \approx \eta(B_y, -B_z)$, i.e., η changes sign with B_y but not with B_z ; (iv) for $\vec{B}_{ip} \parallel \vec{j}$ (panel c) the ratchet effect is suppressed; (v) η depends monotonically on gate voltage, becoming strongly suppressed at $V_g = -2.5$ V, as shown in Fig. 2e.

We interpret these experimental observations as follows: even at very low magnetic fields, a few pinned vortices are present in the array. When the bias current exceeds the depinning threshold, vortices are set in motion, resulting in dissipa-

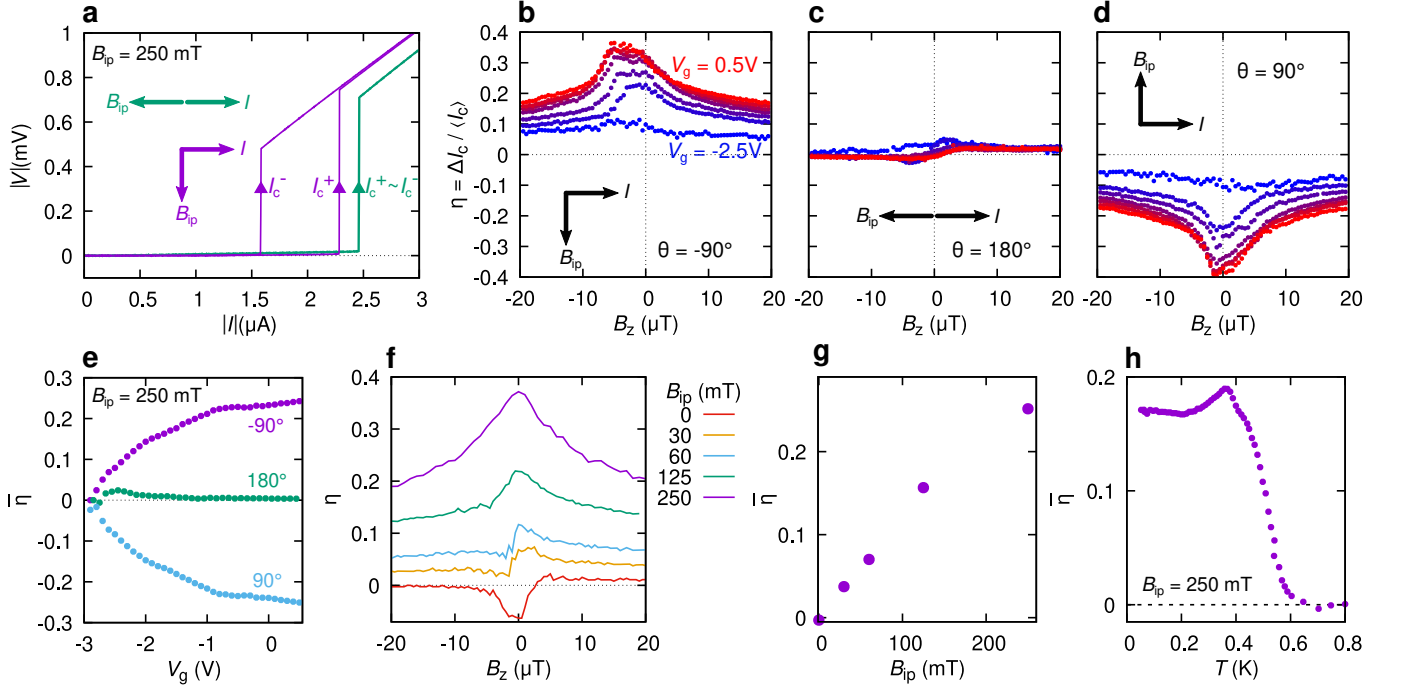


FIG. 2. **a**, Current-voltage characteristics of the 2D Josephson junction array (JJA) for different orientations of the in-plane field, with $B_{ip} = 250$ mT. **b-d**, Rectification efficiency $\eta = \Delta I_c / I_{c, \text{mean}}$ for different orientations (black arrows) of the in-plane field, measured at $B_{ip} = 250$ mT and temperature $T \sim 40$ mK. The color corresponds to different values of the gate voltage V_g , varied in steps of 0.5 V from -2.5 V to 0.5 V. **e**, Average of η (labeled as $\bar{\eta}$) in the range $|B_z| < 20$ μT at $B_{ip} = 250$ mT as a function of gate voltage for different orientations of the in-plane magnetic field. **f**, Rectification efficiency $\eta(B_z)$ for $\theta = -90^\circ$ and gate voltage $V_g = 0.5$ V, for different values of B_{ip} . **g**, $\bar{\eta}$ as a function of B_{ip} , extracted from the data shown in panel **f**. **h**, Temperature dependence of $\bar{\eta}$ for $B_{ip} = 250$ mT, $\theta = -90^\circ$ and gate voltage $V_g = 0.5$ V.

tion and switching to a finite-voltage state. The observations (iii-v) indicate that the rectification efficiency η behaves as φ_0 , since the magnetochiral character and the gate dependence of η are precisely the same as for the anomalous phase shift φ_0 [15]. Importantly, the diode efficiencies of the array and of single junctions are unrelated. For single junctions, the diode efficiency η_{JJ} is already suppressed at moderate fields (above 100 mT in similar samples [7, 12]). Moreover, it is extremely sensitive to temperature, with η_{JJ} being rapidly suppressed for $T > 100$ mK in similar junctions [15]. In contrast, the diode efficiency η of the array remains relatively T -independent up to 0.5 K, as shown in Fig. 2h. It is also proportional to B_{ip} not only for small fields (as, e.g., in Ref. [7]), but also for large B_{ip} as long as a depinning current is measurable (Fig. 2f,g).

After discussing dilute vortices close to zero frustration $|f| \ll 1$, we study how η evolves up to frustration $f = \pm 1$. We probe the vortex dynamics by applying a low frequency ac current bias with amplitude I_{ac} while measuring the first and second harmonic of resistance using digital lock-in amplifiers. This provides a convenient and fast method to measure nonreciprocal response [6, 39]. The second harmonic of the ac response $R_{2\omega} \equiv V_{2\omega} / I_{ac}$ becomes non-zero when the amplitude of the ac current is in the rectification window ($|I_c^-| < I_{ac} < I_c^+$) where $V(I) \neq -V(-I)$. A simulation of $R_\omega(I_{ac})$ and $R_{2\omega}(I_{ac})$ for a current-voltage char-

acteristic with nonreciprocal critical currents is provided in the Supplementary Information. The $R_{2\omega}$ measurement provides better signal-to-noise ratios compared to dc measurements of IV-characteristics. Figure 3a shows the first harmonic $R_\omega \equiv V_\omega / I_{ac}$ as a function of f and I_{ac} , measured for an in-plane field $B_{ip} = 125$ mT at an angle of $\theta = 90^\circ$ with the applied current \vec{I} . A nonzero resistance is observed when I_{ac} exceeds the vortex depinning current, which strongly depends on the applied out-of-plane field. We observe pronounced maxima of the depinning current for the commensurate values of frustration $f = \pm 1/3, \pm 1/2, \pm 2/3, \pm 1$, where vortices form ordered patterns and pinning is strongly increased [16, 40]. $R_{2\omega}$ is shown in Fig. 3b,c for $\theta = \pm 90^\circ$. Peaks of $R_{2\omega}$ with the same sign (blue color in Fig. 3b, red in Fig. 3c) are observed at $f = 0, f = 1/2$, and $f = 1$. A pronounced peak of $R_{2\omega}$ with reversed sign (red color in Fig. 3b, blue in Fig. 3c) is found at $f = 1/3$. The reversed sign can be found in a wider region of frustrations around $f = 1/3$, approximately given by $0.2 \lesssim f \lesssim 0.5$. The sign reversal can be reproduced at a lower in-plane field of 60 mT (Fig. S5 of Supplementary Information). These findings are substantiated when extracting η from IV-measurements for frustrations close to the commensurate values $f = 1/3, 1/2$ and 1, see Fig. 3d-f.

We would like to emphasize a key difference between our *magnetochiral ratchet* effect and the vortex ratchet effect re-

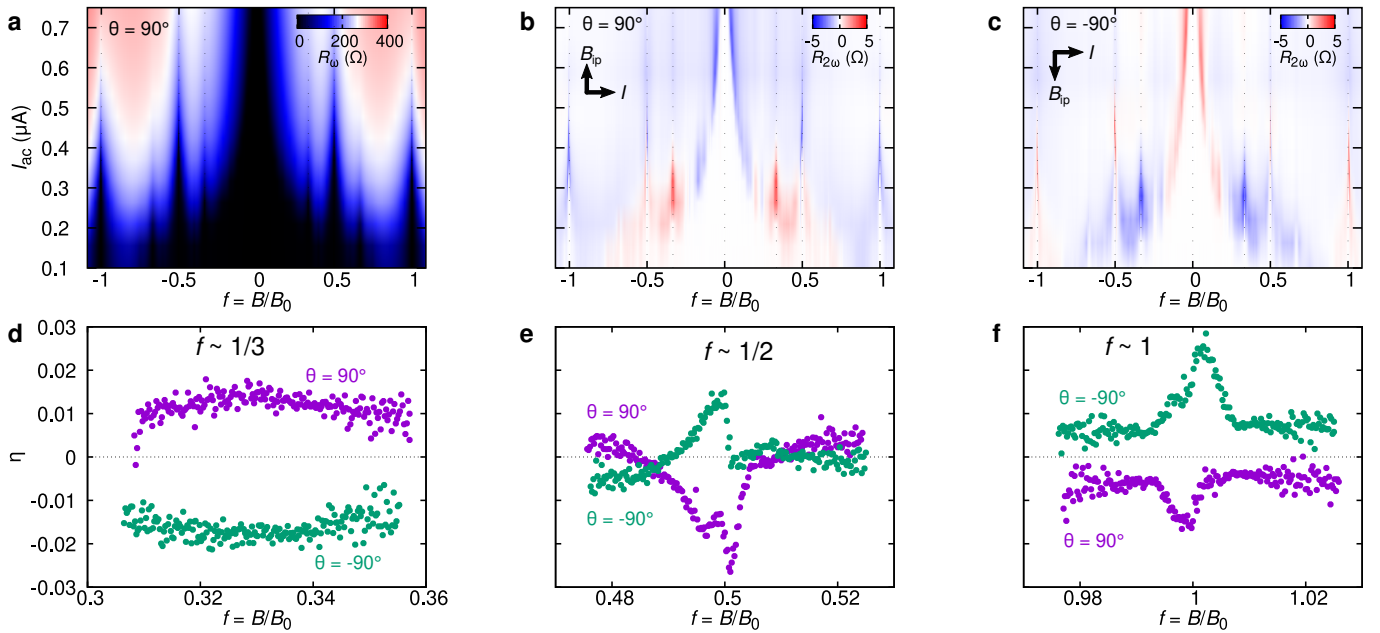


FIG. 3. **a-c**, First harmonic $R_\omega = V_\omega/I_{ac}$ and second harmonic $R_{2\omega} = V_{2\omega}/I_{ac}$ of the resistance measured as a function of frustration and ac bias current. The in-plane field $B_{ip} = 125$ mT is applied perpendicular to the direction of current. **d-f**, Rectification efficiency η around commensurate fields $f = 1/3$, $f = 1/2$, and $f = 1$ obtained from standard $V(I)$ transport measurements. In all plots $T \sim 40$ mK.

ported in previous experiments. So far, a ratchet-like pinning potential was obtained by breaking the real-space symmetry of the system, for example by asymmetrically fabricated pinning sites [41, 42]. Here, the array remains four-fold symmetric (D_4 symmetry) and the symmetry of the pinning potential is reduced to that of a ratchet (D_1) by the combination of SOI, Zeeman field, and diagonal couplings. In our magnetochiral ratchets, the rectification is the same for vortices and antivortices, while it is opposite for asymmetrically fabricated pinning sites [41, 42].

Also the change of sign of the vortex ratchet effect has been previously reported in arrays with asymmetric potential modulation [41–46]. In our case, however, the physics is different: the change of sign we observe is an emergent property of symmetric and periodic arrays, which is evidently related to the particular vortex patterns at commensurate frustration values.

Interestingly, in the limit of small frustrations, the nonreciprocal vortex dynamics can be mapped theoretically to the phase dynamics of a single Josephson diode [47]. The motion of an individual vortex along the \hat{y} direction in the pinning potential is governed by the Langevin equation

$$-\partial_y U - \alpha \dot{y} - \gamma \Phi_0 I = f_y \quad (1)$$

(see Supplemental Information for details, including the geometrical factor γ). The first term describes the pinning force, the second the friction, while the third term corresponds to the Lorentz force exerted by the bias current I in the \hat{x} direction. The Langevin force f_y has zero average and correlator $\langle f_y(t) f_y(t') \rangle = 2\alpha k_B T \delta(t - t')$. Equation (S.12) maps onto the Langevin equation for the phase difference of a single

resistively shunted Josephson junction, with the vortex position becoming the phase difference and the ratchet-like vortex pinning potential turning into the asymmetric current-phase relation.

In conclusion, we observe a magnetochiral vortex ratchet effect in 2D arrays of φ_0 -junctions. The multiterminal character of our junctions introduces competing φ_0 -shifts, leading to frustration and the emergence of spontaneous supercurrent loops in the ground state. These spontaneous currents are ultimately responsible for the nonreciprocity in the depinning current. Our experimental results for $f \ll 1$ are in nice agreement with a minimal model for a 2D square array with nearest and next-nearest-neighbor Josephson couplings, while the sign change at $f = 1/3$ remains an interesting open question.

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Supplementary Information

Magneto-chiral vortex ratchet effect in two-dimensional arrays of φ_0 -Josephson junctions

THEORETICAL METHODS

Model

We model the Josephson junction array as a $N \times N$ square lattice of superconducting islands coupled via Josephson junctions. Each island (labeled by site indices i, j in the x and y directions) is described by the phase $\varphi_{i,j}$ of the superconducting order parameter. To describe the experiment, we transcend standard treatments in two ways:

- In addition to Josephson couplings between nearest neighbors along the x - and y -directions (strength E_J), we also include next-nearest neighbor couplings along the diagonals of the square lattice (Josephson energy E_D). This is motivated by the experimental geometry of square superconducting islands separated by narrow strips of 2DEG, which facilitates Josephson coupling along the diagonal direction.
- We account for the φ_0 -junction behaviour of the horizontal and diagonal junctions, which arises from the interplay of spin-orbit coupling and in-plane magnetic field. Taking the magnetic field along the y -direction, the current-phase relations of both, the horizontal and diagonal junctions are characterized by a phase offset. Since horizontal and diagonal junctions enclose different non-zero angles with the in-plane field, their phase offsets are different and denoted by φ_0^x and φ_0^{diag} , respectively.

Our model Hamiltonian takes the form

$$H = H_0 + H_D, \quad (\text{S.2})$$

$$H_0 = -E_J \sum_{i=1}^{N-1} \sum_{j=1}^N \cos(\varphi_{i+1,j} - \varphi_{i,j} - \varphi_0^x) - E_J \sum_{i=1}^N \sum_{j=1}^{N-1} \cos(\varphi_{i,j+1} - \varphi_{i,j}), \quad (\text{S.3})$$

$$H_D = -E_D \sum_{i,j=1}^{N-1} \left[\cos(\varphi_{i+1,j+1} - \varphi_{i,j} - \varphi_0^{\text{diag}}) + \cos(\varphi_{i+1,j} - \varphi_{i,j+1} - \varphi_0^{\text{diag}}) \right], \quad (\text{S.4})$$

where H_0 accounts for the horizontal and vertical junctions and H_D for the diagonal couplings.

In the absence of the diagonal couplings, the phase offsets φ_0^x are inconsequential, as they do not change the sum of gauge-invariant phase differences around any of the plaquettes. When including the diagonal junctions, there are additional triangular plaquettes. The phase offsets modify the sum of gauge-invariant phase differences around these plaquette by $\pm(\varphi_0^x - \varphi_0^{\text{diag}})$ as illustrated in Fig. S1(a). We can simplify the model and reduce the number of independent parameters by noting that a configuration with zero phase offsets for the diagonal junctions and offsets $\Delta\varphi_0 = \varphi_0^x - \varphi_0^{\text{diag}}$ for the horizontal junctions is gauge equivalent.

The phase offsets modify the ground-state phase configuration $\varphi_{i,j}^{\text{GS}}$. In the limit of large N , we can assume that all phases along a column are aligned as there is no phase bias for the vertical junctions. (Strictly speaking, this assumes that $E_D < E_J$, which is clearly satisfied in experiment.) Denoting

the phase difference between neighboring columns by φ_x , we then have $\varphi_{i,j}^{\text{GS}} = i\varphi_x$. The coupling energies of an island with its three (nearest and next-nearest) neighbors to the right [see Fig. S1(b) for an illustration] is uniform across the entire array, so that the ground-state phase configurations minimizes

$$h(\varphi_x) = -E_J \cos(\varphi_x - \Delta\varphi_0) - 2E_D \cos \varphi_x. \quad (\text{S.5})$$

This yields

$$\varphi_x = \arctan\left(\frac{E_J \sin \Delta\varphi_0}{E_J \cos \Delta\varphi_0 + 2E_D}\right), \quad (\text{S.6})$$

so that the ground-state phase configuration can be written explicitly as

$$\varphi_{i,j}^{\text{GS}} = i \arctan\left(\frac{E_J \sin \Delta\varphi_0}{E_J \cos \Delta\varphi_0 + 2E_D}\right). \quad (\text{S.7})$$

We have confirmed for various parameters E_D and $\Delta\varphi_0$ that this is consistent with numerical results obtained by minimizing the energy of the entire array.

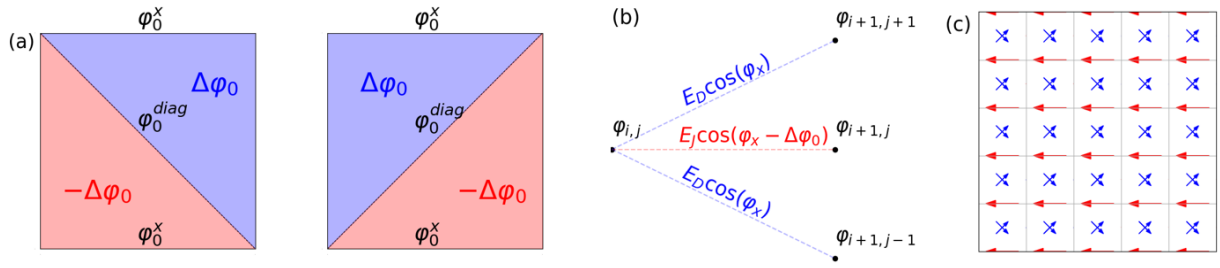


FIG. S1. Model Hamiltonian with φ_0 -junctions and diagonal couplings. (a) Phase configuration inside of a plaquette. Due to the diagonal couplings and the phase offsets of the junctions, the system is effectively subject to a transverse magnetic flux $\Delta\varphi_0 = \varphi_0^x - \varphi_0^{diag}$ in the blue region and $-\Delta\varphi_0$ in the red region. (b) Illustration of the ground-state calculation. Only an elementary cell involving four superconducting islands need to be considered due to translational symmetry in the x - and y -directions. (c) Current configuration of the ground state. The arrows indicate the currents between the respective nodes. The length of the arrows indicates the magnitude of the current, with the critical current corresponding to an arrow connecting the nodes. Parameters: $E_D = 0.5E_J$, $\Delta\varphi_0 = \pi/2$.

The phase configuration implies that the diagonal couplings along with the phase offsets lead to currents flowing in the ground state, namely $I_h = (2eE_J/\hbar) \sin(\varphi_x - \Delta\varphi_0)$ along the horizontal bonds and $I_d = (2eE_D/\hbar) \sin \varphi_x$ along the diagonal bonds. This is illustrated in Fig. S1(c). We note that the currents break the mirror symmetry with respect to the vertical axis as well as time-reversal symmetry, which is conducive for a diode effect.

Vortex potential

The experiment suggests that a low density of vortices is present even at nominally vanishing perpendicular magnetic field. We consider the dynamics of a single vortex with given circulation.

We first approximate the phase configuration in the presence of a vortex by [36]

$$\varphi_{i,j}(x, y) = \varphi_{i,j}^{GS} + \varphi_{i,j}^v(x, y), \quad (\text{S.8})$$

where

$$\varphi_{i,j}^v(x, y) = \arctan\left(\frac{j-y}{i-x}\right). \quad (\text{S.9})$$

This neglects relaxation effects due to the interplay of the ground-state currents with the vortex configuration. (In the next section, we will go beyond this approximation.)

We can use this ansatz to calculate the potential energy U of the vortex as a function of its position (x, y) (taken to be continuous) through

$$U(x, y) = H(\{\varphi_{i,j}(x, y)\}). \quad (\text{S.10})$$

Here, H denotes the Hamiltonian in Eq. (S.2). For $E_D = 0$ and $\Delta\varphi_0 = 0$, we reproduce the results of Ref. [36] as shown in Fig. S2(a). The potential minima are located in the center of the plaquettes, while the maxima sit at the superconducting sites.

Turning on the diagonal couplings as well as the phase offsets leads to significant modifications of the vortex potential,

as shown in Fig. S2(b) for $E_D = 0.5E_J$ and $\Delta\varphi_0 = \pi/2$. The minima are shifted away from the plaquette centers along the y -direction. The associated deformation of the potential breaks the mirror symmetry about the x -axis. These differences are further illustrated by line cuts of the potential and its derivative as shown in Fig. S2(c,d). These cuts are along lines of fixed x , with x taken at the center of the plaquette. The diagonal couplings clearly shift the minima of the potential. Moreover, the maximal positive derivative of U along the y -direction becomes smaller than the maximal negative derivative, reflecting a tendency of the potential to form a ratchet [Fig. S2(d)]. In addition, finite-size effects lead to a monotonously changing shift of the potential across the sample, which implies asymmetric upward and downward barriers.

The ratchet-like vortex potential implies diode behavior of the depinning current. Applied currents to the right (left) tilt the vortex potential in opposite directions. Depinning occurs once the tilted vortex potential no longer exhibits minima, i.e., when the tilt becomes equal to the minimal (maximal) derivative of the potential in the absence of a bias current.

Langevin equation for vortex motion and diode effect

Following Ref. [36], the dynamics of the vortex in the array can be described by a Langevin equation, which takes the same form as the Langevin equation for the phase difference of a single junction [48]. Interestingly, this also allows for relating the diode effect of the array to a diode effect in single junctions [47].

We focus on the vortex position y along the y -axis, assuming overdamped Josephson junctions. In addition to the force $-\nabla U$ due to the vortex potential, the vortex experiences a Lorentz force [49]

$$\mathbf{F}_L = \gamma\Phi_0(\mathbf{I} \times \hat{\mathbf{z}})/a \quad (\text{S.11})$$

exerted by the externally applied current I per lattice site. Here, $\Phi_0 = h/2e$ is the superconducting flux quantum, a the lattice constant of the Josephson junction array, and γ a geometrical

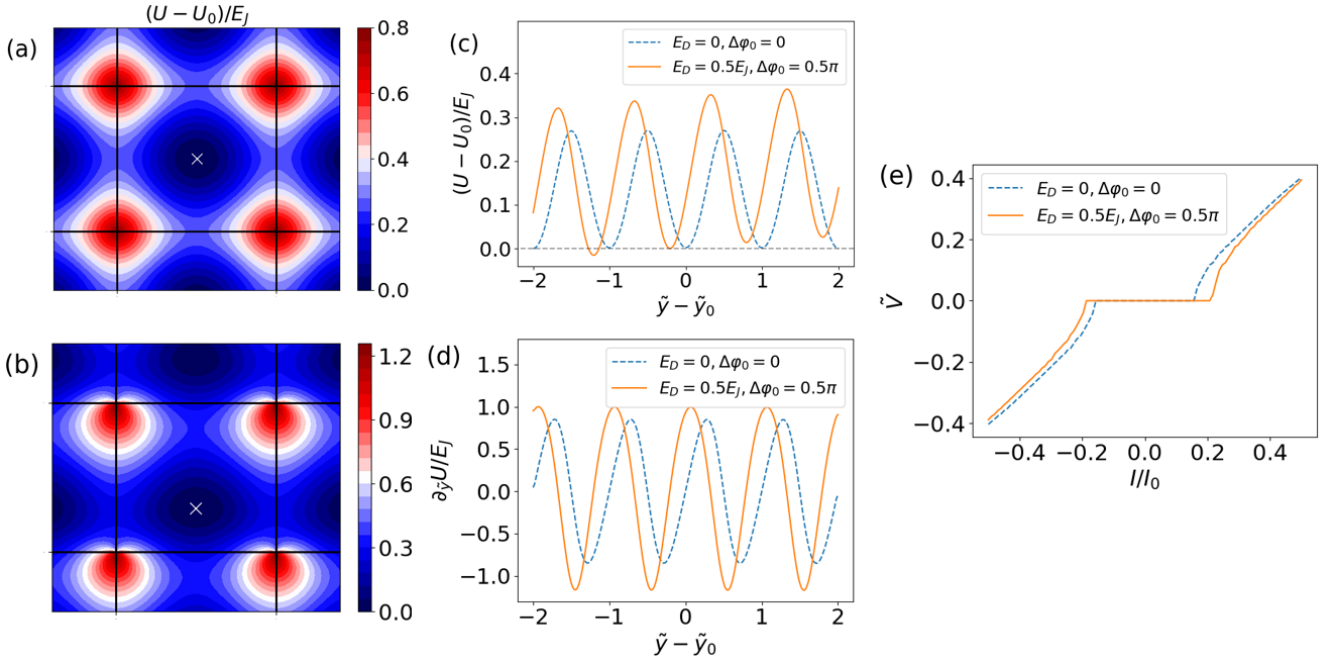


FIG. S2. Vortex in a Josephson junction array with φ_0 -junctions and diagonal couplings. (a) Contour plot of the vortex potential $U(x, y)$ with $E_D = 0$ and $\Delta\varphi_0 = 0$. The black lines indicate the Josephson junction array, the white cross shows the minimum of the potential. (b) Same plot as (a) with $E_D = E_J/2$ and $\Delta\varphi_0 = \pi/2$. (c) Plot of the vortex potential $U(x_0, y - y_0)$ as a function of y , with (x_0, y_0) denoting coordinates of the array center. Parameters corresponding to both (a) and (b). For easier comparison, we subtract a constant U_0 corresponding to the potential at the minimum closest to the array center. (d) y -derivatives of the potential as a function of y corresponding to (c). (e) $I - V$ curves for both parameter sets calculated from the Langevin equation in Eq. S.12. The depinning currents correspond to the extreme values in (d) weighted by the reduction parameter γ . We calculated the voltage for 200 current values between $-I_0/2$ and $I_0/2$. Further parameters: $\tau = 0.05$, $n_{\max} = 2000$.

factor discussed below. Moreover, a friction force due to quasiparticle currents (friction constant α), and the associated fluctuating Langevin force \mathbf{f} act on the vortex. The Langevin equation for $y(t)$ takes the form

$$-\partial_y U - \alpha \dot{y} - \gamma \Phi_0 I / a = f_y. \quad (\text{S.12})$$

The Langevin force is characterized by a zero average and correlator $\langle f_y(t) f_y(t') \rangle = 2\alpha k_B T \delta(t - t')$ at temperature T . For a large uniform array with a (small) average vortex density n , the electric field E in the x -direction takes the form [50]

$$E = -\Phi_0 n \bar{v}, \quad (\text{S.13})$$

related to the the average drift velocity \bar{v} of the vortex along y .

We now discuss the geometric factor γ . The current carried by the horizontal junctions exerts a Lorentz force on the vortices, which points along the y -direction, whereas the currents flowing through the diagonal junctions exert a force, which is rotated by $\pm 45^\circ$. While their x -components cancel (allowing us to focus on the y -direction), their y -components contribute to the total Lorentz force F_L . Computing the current distribution, we find $F_L = -\gamma \Phi_0 I / a$ with

$$\gamma = \frac{E_J + \sqrt{2} E_D}{E_J + 2E_D} \quad (\text{S.14})$$

in the limit of small phase offsets.

We can rewrite the Langevin equation in terms of a phase parameter defined through $\theta = 2\pi y/a$. In this case, the Langevin equation for the vortex maps directly on the Langevin equation for the phase across a single current-biased junction within the resistively shunted Josephson-junction model,

$$-\frac{2e}{\hbar} \partial_\theta U(\theta) - \frac{\hbar}{2eR} \dot{\theta} - I_{\text{bias}} = \delta i \quad (\text{S.15})$$

with $\langle \delta i(t) \delta i(t') \rangle = (2k_B T/R) \delta(t - t')$. The mapping uses the identifications $R \leftrightarrow \Phi_0^2/a^2 \alpha$ for the shunt resistance and $I_{\text{bias}} \leftrightarrow \gamma I$ for the bias current. The Josephson energy $U(\theta)$ can be directly identified with the vortex potential. Finally, the voltage $V = (\hbar/2e) \dot{\theta}$ across the single junction is related to the electric field E in the uniform array according to $V \leftrightarrow E/(na)$. According to this mapping, the Josephson diode effect is encoded in the structure of $U(\theta)$ for both, single junctions and arrays.

For numerical calculations, we discretize the time dependence of the vortex position y and rewrite the Langevin equation in Eq. S.12 in dimensionless units. At temperature $T = 0$, it takes the form

$$-\frac{1}{2\pi} \frac{d\tilde{U}}{d\tilde{y}} - \frac{d\tilde{y}}{d\tilde{t}} - \gamma \tilde{I} = 0. \quad (\text{S.16})$$

Here we introduced dimensionless variables (indicated by a tilde) through $U = E_J \tilde{U}$, $y = \alpha \tilde{y}$, $t = (\alpha a^2 / 2\pi E_J) \tilde{t}$ as well as $I = I_0 \tilde{I}$, where $I_0 = 2\pi E_J / \Phi_0$ is the critical current per plaquette. We further use Eq. S.13 to define a dimensionless voltage \tilde{V} per plaquette through

$$V = \frac{2\pi E_J \Phi_0 n}{\alpha} \tilde{V}. \quad (\text{S.17})$$

The voltage \tilde{V} can be obtained from the Langevin equation via

$$\tilde{V} = -\frac{\overline{d\tilde{y}}}{d\tilde{t}}, \quad (\text{S.18})$$

where the bar indicates a time average. The time-averaged vortex velocity in dimensionless units is obtained from the Langevin equation as a function of the bias current \tilde{I} and two dimensionless parameters, the ratio E_D/E_J of Josephson energies and the phase offset φ_0 .

The calculated $V-I$ characteristic is displayed in Fig. S2(e). For $E_D = 0$ and $\Delta\varphi_0 = 0$, we find a current-voltage characteristic akin to that of a conventional single junction. Setting $E_D = E_J/2$ and $\Delta\varphi_0 = \pi/2$, the positive and negative depinning currents increase asymmetrically due to the increases in the maximum and minimum of $\partial_y U$, consistent with the diode effect observed in the experiment.

Depinning currents with phase relaxation

We now go beyond the arctan approximation of the vortex configuration (Eq. S.8) and allow for relaxation of the phase configuration, using a gradient-descent scheme. We tilt the washboard potential of the Hamiltonian in Eq. S.2,

$$H_I = H + \frac{\hbar}{2e} I \sum_{j=1}^N (\varphi_{1,j} - \varphi_{N,j}) \quad (\text{S.19})$$

for an applied current I in the x -direction. For small I , we minimize the energy for phase configurations containing a single vortex. We start with the phase configuration $\varphi_{i,j}(x_0, y_0)$ in Eq. S.8 with an (unrelaxed) vortex located at the center (x_0, y_0) of the array, and gradually evolve the system towards the local minimum via a standard gradient-descent scheme.

The system monotonically converges to a stable solution, as long as the current I remains below the depinning current I_c . Beyond the depinning current, the vortex keeps hopping along the y -direction. We start with a small current. If the vortex remains in its initial plaquette after n_{max} 'time' steps of length τ , the current is below the depinning current. We then repeat the descent scheme for a slightly larger current, continuing in k small increments up to a current density of I_{max} . We identify the depinning current I_c with the current, for which the vortex no longer remains in the initial plaquette. We implement the procedure for currents of both signs.

Our results are shown in Fig. S3. Fig. S3(a) displays the current configuration for a relaxed vortex in the presence of

diagonal couplings and phase offset. The plaquette containing the vortex hosts diagonal currents. We observe that the current circulates only around the two lower triangles of the plaquette (as highlighted in the figure). This indicates that the position of the vortex is shifted away from the center of the plaquette in the negative y -direction. This is consistent with the vortex potential shown in Fig. S2(b).

Figure S3(b) shows the depinning currents I_c^+ and I_c^- as a function of the phase offsets $\Delta\varphi_0$ for two values of the diagonal couplings E_D . The direction of the currents is indicated by color. We find that the depinning currents for both directions are reduced with increasing $\Delta\varphi_0$, but their asymmetry becomes stronger. The asymmetry is quantified by the diode efficiency

$$\eta = 2 \frac{I_c^+ - I_c^-}{I_c^+ + I_c^-}, \quad (\text{S.20})$$

which is shown in Fig. S3(c). The diode efficiency monotonically increases with both E_D and $\Delta\varphi_0$.

We also computed the depinning currents I_c^{\parallel} in the y -direction, which do not exhibit a diode effect, consistent with the absence of a symmetry breaking in this direction. Moreover, I_c^{\parallel} increases with phase offset $\Delta\varphi_0$. This is in contrast to the depinning current I_c^{\perp} in the x -direction (averaged over current directions), which decreases with $\Delta\varphi_0$. This is shown in Fig. S3(d). We note that unlike the arctan approximation (via the geometric factor γ), the phase-relaxation approach is no longer limited to small phase offsets.

EXPERIMENTAL METHODS

The configuration of vortices in the array and the superconducting contacts will in general depend on the history of the out-of-plane magnetic field. Field-cooling is required to obtain an equilibrium configuration of vortices. The data presented in the main text has been obtained with the following field-cooling procedures:

- Fig. 2 **e**: field-cooling at every value of B_z
- all other panels of Fig. 2: field-cooling in zero out-of-plane field before the measurement
- Fig. 3 **a-c**: no field cooling
- Fig. 3 **d-f**: field-cooling at the commensurate fields ($f = 1/3, 1/2, \text{ and } 1$) before the measurement

DEVICE LAYOUT AND CHARACTERIZATION

The used semiconductor/superconductor layer stack is described and characterized in the supplemental information of our previous work [15], which also describes the details of fabrication. The layout of devices A and B is shown in Fig. S4 **a**. The arrays consist of 200×200 square islands with a lattice constant $a = 500$ nm. The junctions between the islands have a

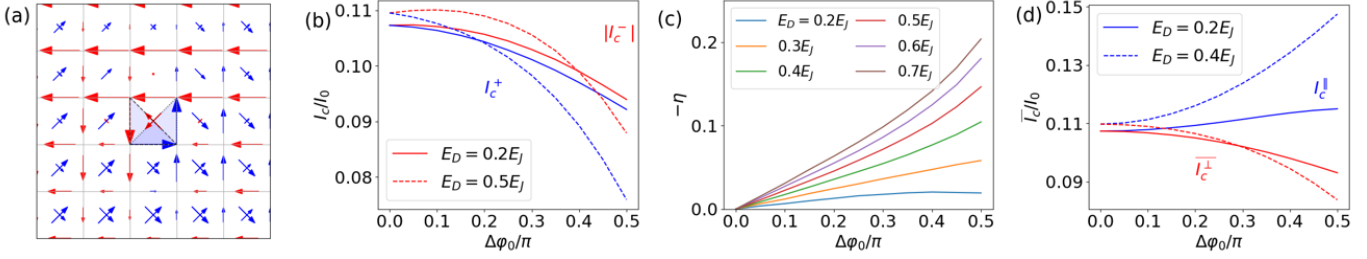


FIG. S3. Depinning currents with phase relaxation. (a) Current distribution for a relaxed vortex configuration. The length of arrows indicates the magnitude of the currents. Notice that in the central plaquette, the currents circulate around the highlighted triangles, reflecting the shift of the vortex minimum into the lower half of the plaquette. (b) Positive and negative depinning currents as a function of $\Delta\phi_0$ for two values of E_D . (c) Diode efficiency defined in Eq. S.20 as a function of $\Delta\phi_0$ for various values of E_D . (d) Comparison of depinning current parallel (in blue) and perpendicular (in red; averaged over current directions) to the applied in-plane magnetic field as a function of E_D and $\Delta\phi_0$. Parameters: $n_{max} = 10^5$, $\tau = 0.2$, $k = 1200$. For horizontal currents: $I_{min} = 0.06I_0$, $I_{max} = 0.12I_0$. For vertical currents: $I_{min} = 0.09I_0$, $I_{max} = 0.15I_0$.

length of ~ 100 nm. Measurements are performed in a dilution refrigerator with a base temperature of $T \sim 35$ mK. Details of the measurement setup can be found in the supplemental information of [15]. Unless stated otherwise, measurements are performed on device A.

The electron density in the semiconductor quantum well can be found from magnetoresistance measurements performed with the array sample. The used magnetic fields are far above the critical field of the aluminum superconductor ($B_c \approx 100$ mT). Fig. S4 c shows the differential resistance of the array as a function of out-of-plane magnetic field for different gate voltages. Fig. S4 d shows the same data after removing a second-order polynomial background with clearly visible Shubnikov de-Hass (SdH) oscillations. The density corresponding to the oscillations is $9.0 \times 10^{11} \text{ cm}^{-2}$ with no apparent dependence on gate voltage. This indicates that the SdHs probe the electron density in the semiconductor covered by Al, where the effect of the gate is screened. The obtained density is in excellent agreement with the value $n = 8.5 \times 10^{11} \text{ cm}^{-2}$ found by recent cyclotron resonance measurements on a similar wafer [51]. The linear part of the magnetoresistance is caused by the two-terminal measurement, where voltage is probed on the terminals which are used to source the current. The two-terminal resistance will probe both the longitudinal resistance and the Hall resistance [52].

The temperature dependence of zero-bias differential resistance of the array is shown in Fig. S4 e. A small decrease of resistivity is found below the critical temperature of the film $T_{c,Al} \sim 2.1$ K. The onset of Josephson coupling is found below 1.1 K. The differential resistance at $T \approx 40$ mK as a function of out-of-plane field and bias current is shown in Fig. S4 b. We find pronounced peaks of the depinning currents at the integer frustration $f := B_z/B_0 = \pm 1$ with the matching field $B_0 = \pm\Phi_0/a^2 \sim 8.2$ mT. Additional peaks are found at various fractions of the frustration parameter, with the most pronounced peaks at $f = 1/2$, $f = 1/3$, and $f = 2/3$.

The range of the vortex-vortex interaction in a 2D JJA is

related to the magnetic penetration depth

$$\lambda_{\perp} = \frac{\Phi_0}{2\pi\mu_0 I_c} \quad (\text{S.21})$$

where I_c is the critical current of a single junction. For a JJ of width 500 nm we expect $I_c \sim 500$ nA in zero magnetic field, which yields $\lambda_{\perp} \sim 500$ μm . As this largely exceeds the dimensions of the device, we do not have to take screening effects into account.

IV-CHARACTERISTICS AT LOW MAGNETIC FIELD

Fig. S5 shows current-voltage characteristics obtained around zero and integer frustration. In order to avoid hysteresis from non-equilibrium flux pinning in the array and the superconducting contacts, we perform field cooling for each value of the out-of-plane field.

The $V(I)$ curves feature discontinuous jumps with a large hysteresis between up and down sweep of the current. The hysteresis is likely caused by heating due to the large power dissipation in the resistive state. For fields below ~ 2 μT we observe a direct jump between the zero voltage state (black/dark blue in Fig. S5 c) and the voltage state. For higher out-of-plane field we find a regime of flux creep with approximately constant slope of $V(I)$, followed by the jump into the resistive state. The discontinuous jump into the resistive state is also found around integer frustration, as shown in Fig. S5 d. As expected for vortex depinning, the observed depinning current densities are a factor of 10 below the Josephson critical current densities obtained using single junction devices made with material from the same wafer [15]. We conclude that the measured critical current is always caused by depinning of vortices, even in nominally zero out-of-plane field. The field $\Phi_0/A \approx 200$ nT corresponding to a single vortex in the array is below the resolution of the out-of-plane field used in our measurements.

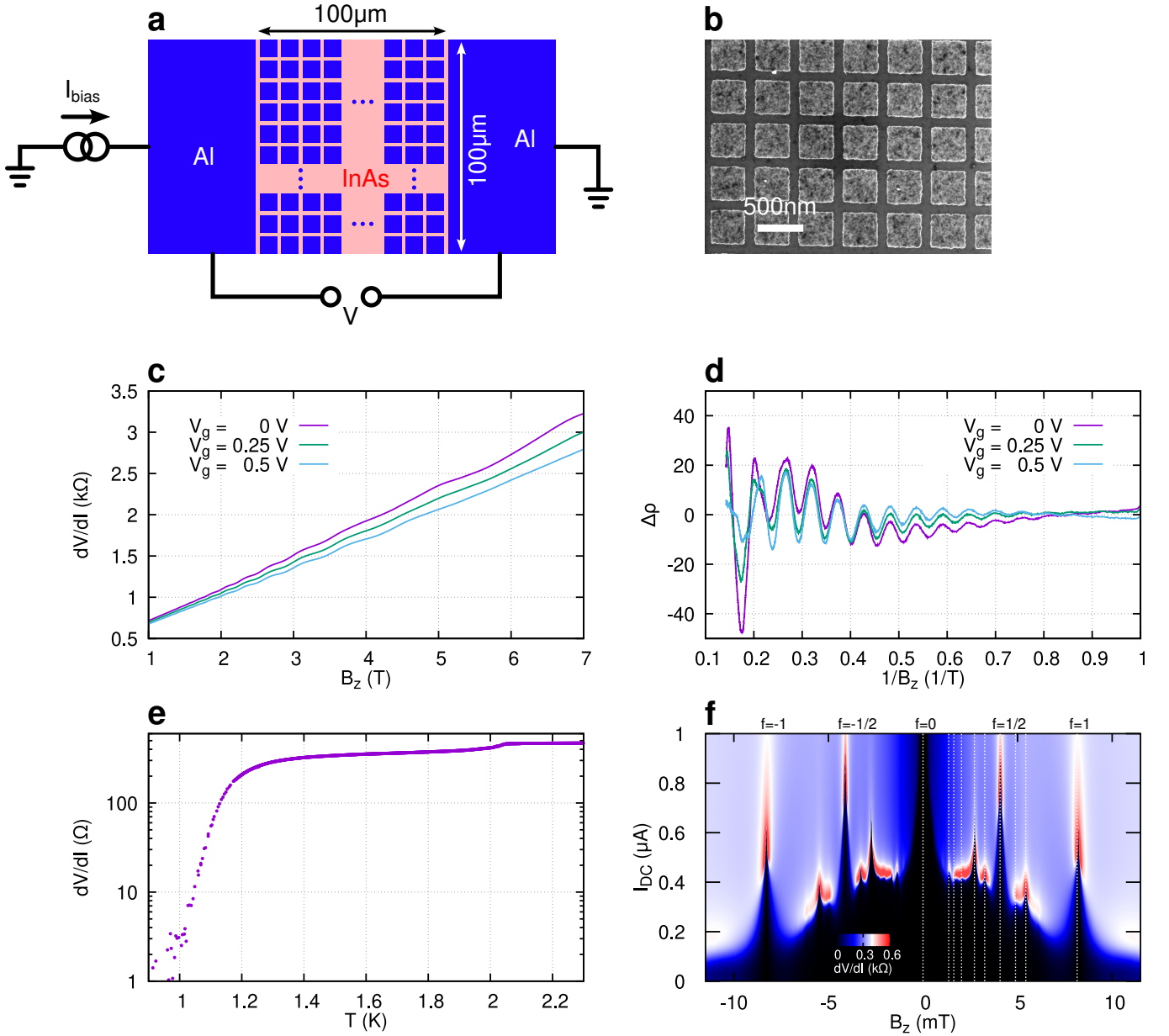


FIG. S4. **a**, Device geometry of devices A and B. **b**, Scanning electron microscope image of device A. **c**, Two-point measurement of magnetoresistance in the normal state as a function of out-of-plane magnetic field. The temperature is $T \sim 200$ mK. **d**, Magnetoresistance data after subtraction of a quadratic polynomial background, plotted as a function of $1/B_z$. **e**, Temperature dependence of zero-bias differential resistance at zero magnetic field. **f**, Differential resistance at zero in-plane field and $T \sim 40$ mK measured as a function of out-of-plane field and dc bias current. Peaks of the depinning current are found at the indicated dotted lines at $f = B_z/B_0 = 0, 1/6, 1/5, 1/4, 1/3, 2/5, 2/3, 1$. The measurement is performed with an ac-excitation of 10 nA at frequency 777 Hz.

ADDITIONAL DATA ON NON-RECIPROCAL DEPINNING CURRENT

Fig. S6 **a,b** show the angle dependence of the depinning current and the diode efficiency for an in-plane field of 250 mT. The averaged depinning current shows pronounced maxima when the field is parallel to the current ($\theta = 0, \pi$) and minima when the field is perpendicular to the current ($\theta = \pi/2, 3\pi/2$). The angle dependence of the averaged diode efficiency shows

the sinusoidal behaviour $\bar{\eta} \sim -\sin(\theta)$. Fig. S6 **c** shows the depinning current as a function of the in-plane magnetic field, corresponding to Fig. 2 **f** of the main text. We compare the non-reciprocal depinning current of devices A and B at an in-plane field of $B_{ip} = 250$ mT (Fig. S6 **d,e**). The depinning current is slightly lower for device B. The magnitude of the diode efficiency of the both devices is nearly equal.

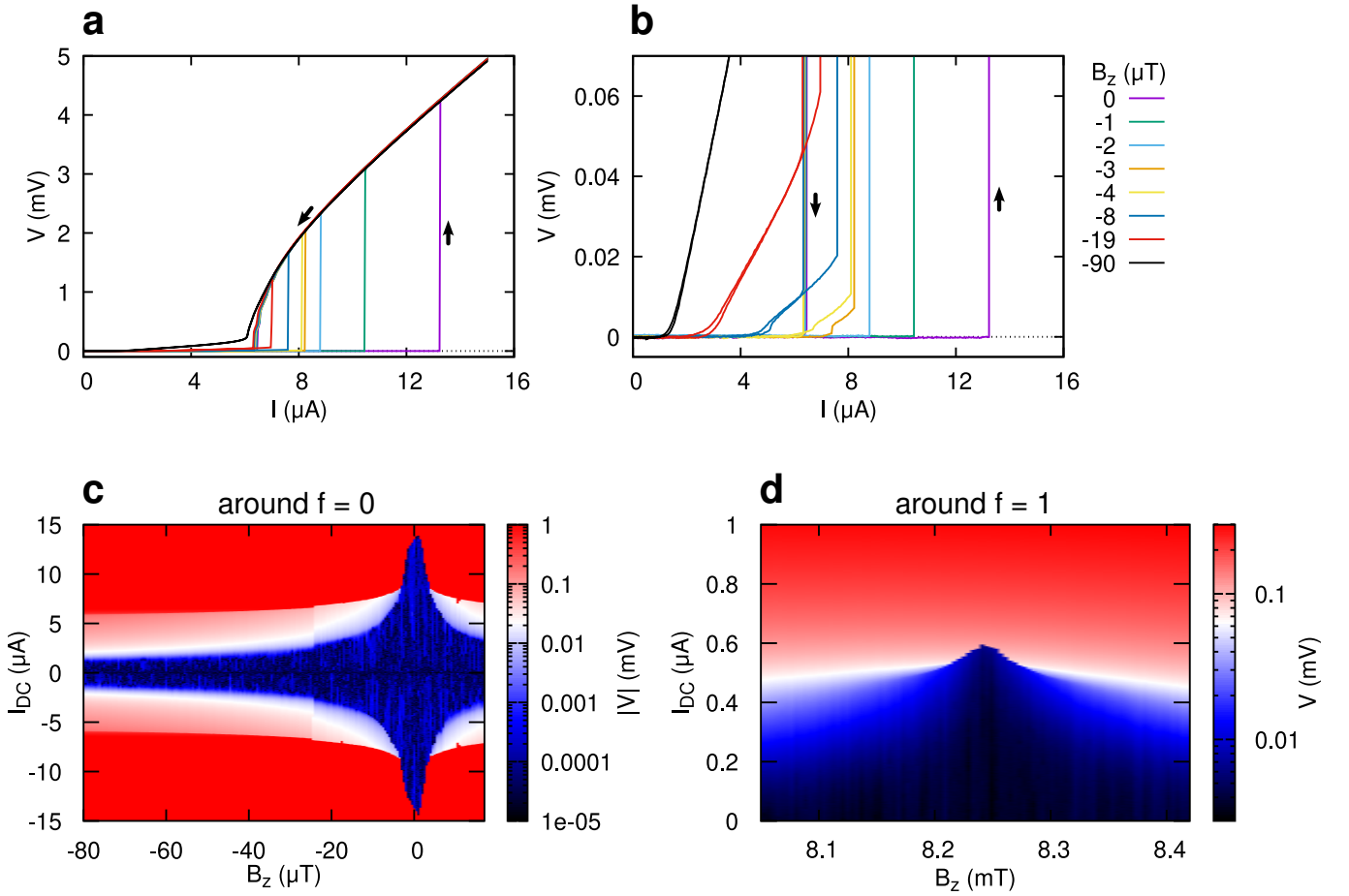


FIG. S5. **Current-voltage characteristics at zero in-plane magnetic field around $f = 0$ and $f = 1$** **a**, $V(I)$ curves for low out-of-plane fields. Black arrows indicate the sweep direction, showing the hysteresis between up and down sweep of the current. Field-cooling is performed for every value of B_z and $V(I)$ measurements always start at zero bias current. **b**, Zoom into the low voltage part of **a**. **c**, Color map of $\log(V(B_z, I))$ around zero frustration. **d**, Color map of $\log(V(B_z, I))$ around integer frustration $f = 1$.

ADDITIONAL DATA ON NON-RECIPROCAL RESISTANCE

Fig. S7 **b** shows the expected behavior of R_ω and $R_{2\omega}$ for the $V(I)$ curve shown in Fig. S7 **a** with $I_c^+ > |I_c^-|$. $R_{2\omega}$ is positive when the amplitude I_{ac} of the sinusoidal excitation current is in the rectification window between negative and positive depinning current.

Fig. S8 **a-c** show linetraces of $R_\omega(f)$ and $R_{2\omega}(f)$, cor-

responding to Fig. 3 **a-c** of the main text. No pronounced peak is present at $f = 0$, as the maximum excitation current $I_{ac} = 0.8 \mu\text{A}$ is far below the depinning currents at $f = 0$. Additional measurements of R_ω and $R_{2\omega}$ are performed at $B_{ip} = 60$ mT. The resulting data is shown in Fig. S8 **d,e**. As for the case with $B_{ip} = 125$ mT, we find a pronounced sign-reversal of $R_{2\omega}$ around $f = 1/3$.

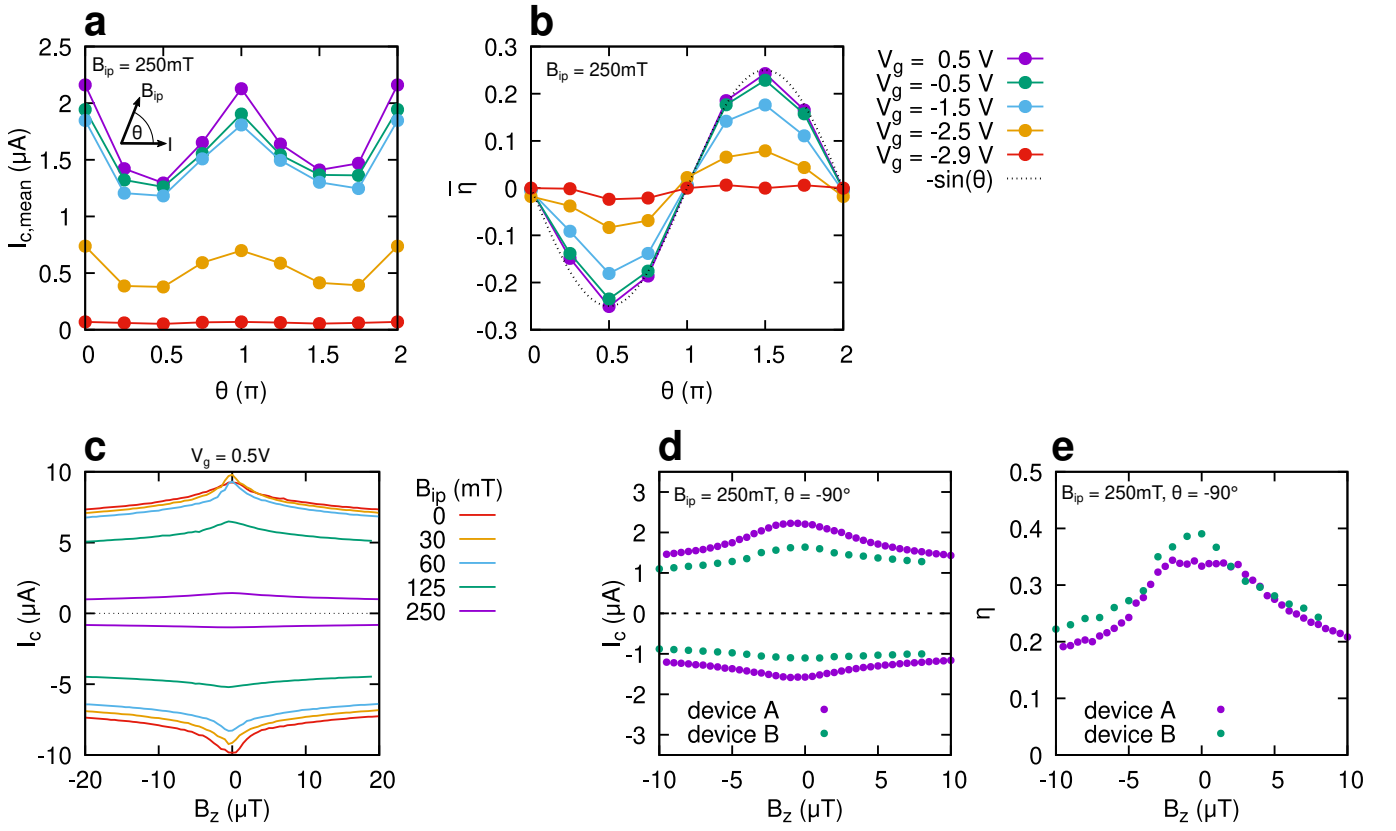


FIG. S6. **Additional data on non-reciprocal depinning current.** **a**, Angle dependence of the mean depinning current $1/2(I_c^+ + I_c^-)$. The depinning current is averaged over the range $|B_z| < 20 \mu\text{T}$. **b**, Angle dependence of the averaged diode efficiency η . **c**, Depinning current as a function of out-of-plane field for different magnitudes of the in-plane field ($\theta = -90^\circ$). **d,e**, Comparison of depinning current and diode efficiency for the nominally identical devices A and B.

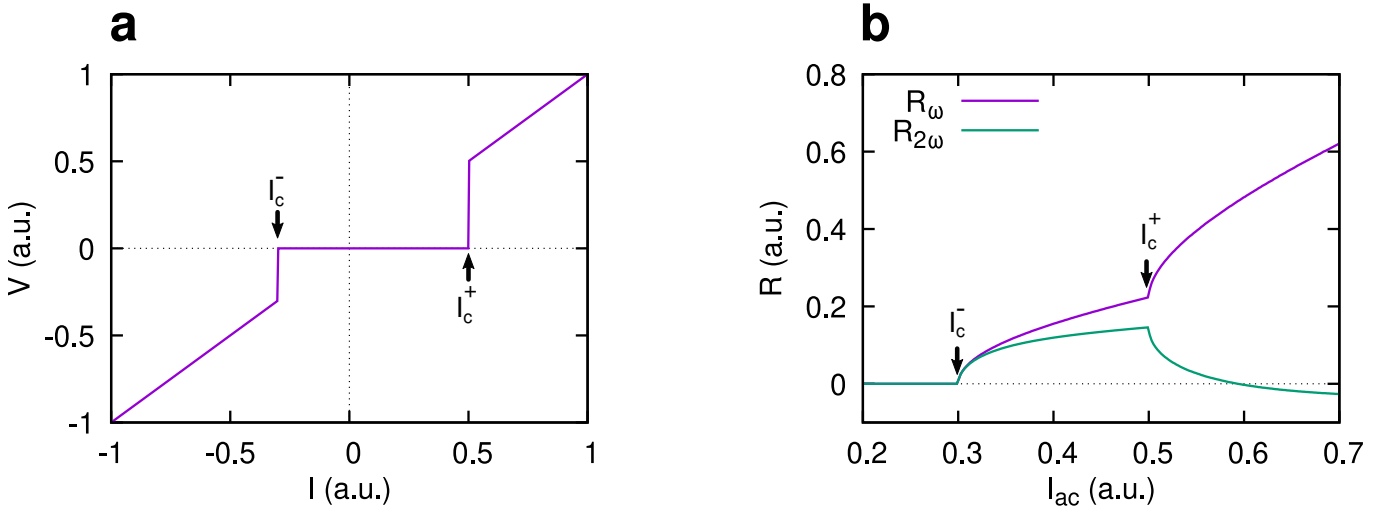


FIG. S7. **Simulation of non-reciprocal resistance.** **a**, Non-reciprocal $I(V)$ characteristic with $\eta = \Delta I_c / I_{c,\text{mean}} = 0.5$. **b**, Numerically calculated first and second harmonic of resistance for an ac current bias with amplitude I_{ac} .

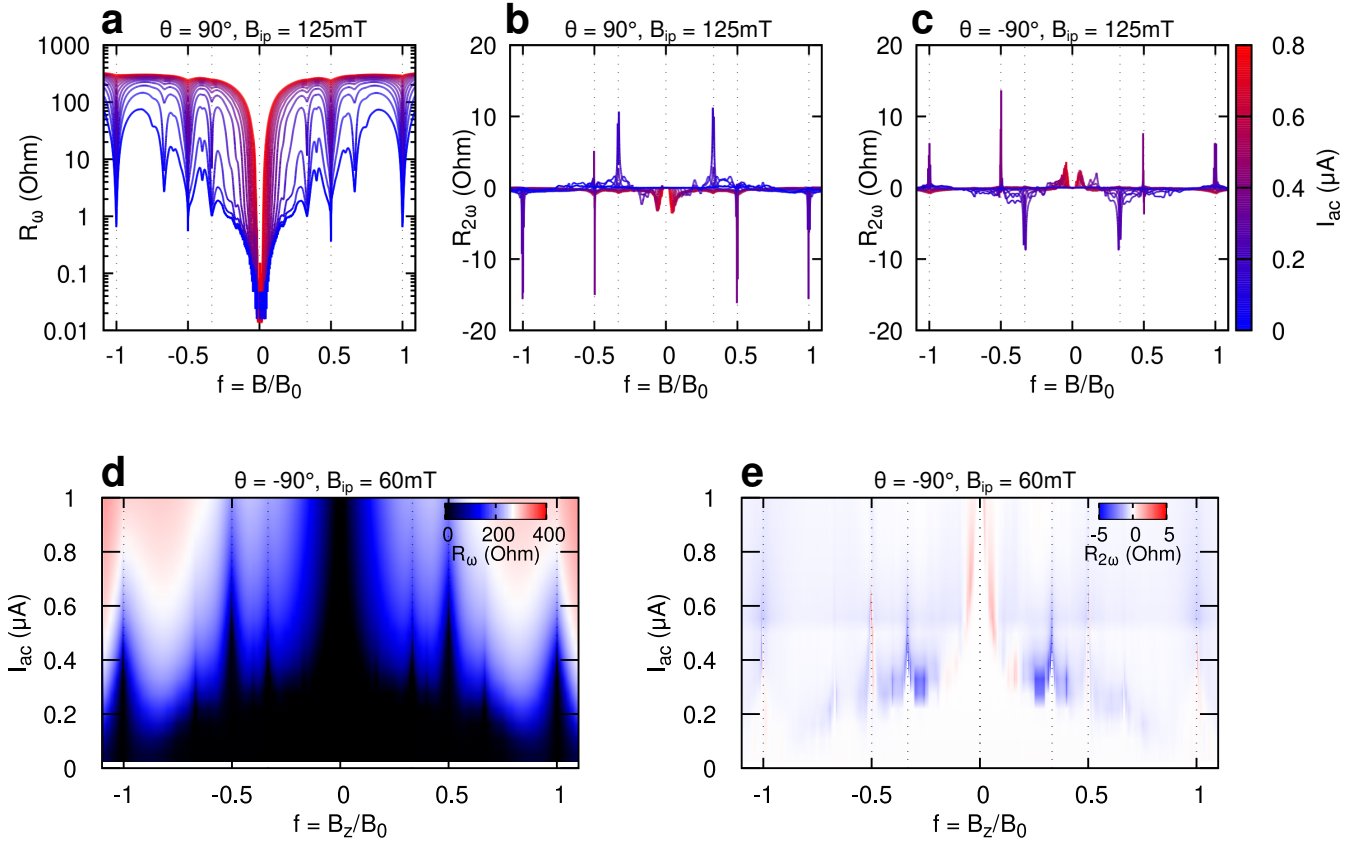


FIG. S8. **Additional measurements of non-reciprocal resistance as a function of frustration.** a-c, Same data as in Fig. 3 a-c of the main text showing $R_\omega(f)$ and $R_{2\omega}(f)$. Different colors correspond to different ac current excitations. d,e, First and second harmonic of resistance measured at $B_{ip} = 60\text{mT}$. $R_{2\omega}$ shows the sign-reversal in a region of frustration around $f = 1/3$.